

Insulated-Gate Bipolar Transistors (IGBTs) — Single

Part Number	Package	Configuration	V _{CE} (max) (V)	I _C (max) (A)		V _{GE(sat)} (typ) (V)	E _{ON} (typ) (mJ)	E _{OFF} (typ) (mJ)	Q _g (typ) (nC)
				25°C	100°C				
TO-247									
AOKS30B60D1	TO-247	IGBT	600	60	30	2	1.1	0.24	34
AOKS40B65H2AL	TO-247	IGBT	650	80	40	2.05	1.17	0.54	61
AOKS40B60D1	TO-247	IGBT	600	80	40	1.85	1.55	0.3	45